

Fuji Discrete Package IGBT

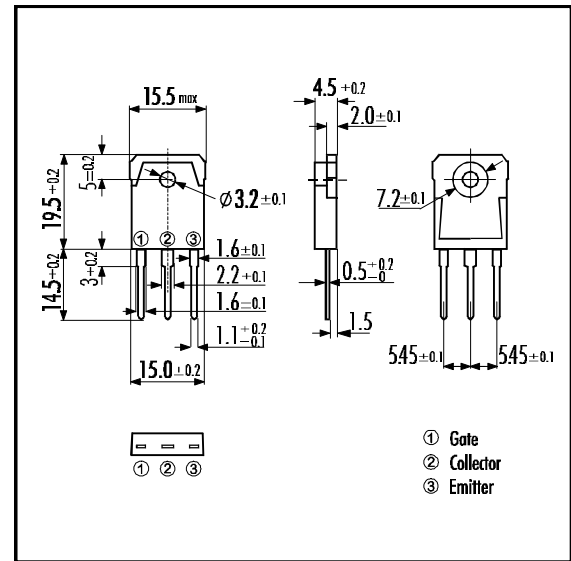
■ Features

- Square RBSOA
- Low Saturation Voltage
- Less Total Power Dissipation
- Minimized Internal Stray Inductance

■ Applications

- High Power Switching
- A.C. Motor Controls
- D.C. Motor Controls
- Uninterruptible Power Supply

■ Outline Drawing

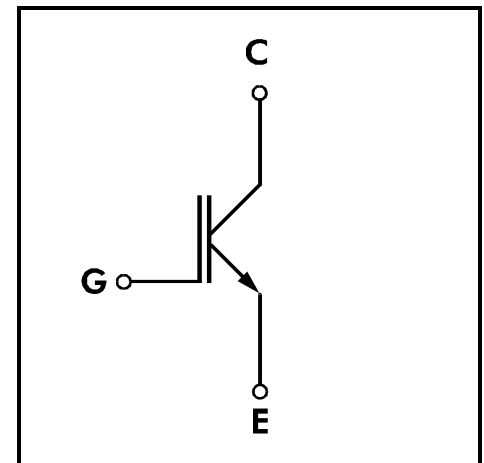


■ Maximum Ratings and Characteristics

• Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Items	Symbols	Ratings	Units
Collector-Emitter Voltage	V_{CES}	1200	V
Gate -Emitter Voltage	V_{GES}	± 20	V
Collector Current	DC $T_c=25^\circ\text{C}$	I_{C25}	16
	DC $T_c=100^\circ\text{C}$	I_{C100}	10
	1ms $T_c=25^\circ\text{C}$	I_{CPULSE}	48
IGBT Max. Power Dissipation	P_C	135	W
Operating Temperature	T_j	+150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 ~ +150	$^\circ\text{C}$
Mounting Screw Torque		50	Nm

■ Equivalent Circuit



• Electrical Characteristics (at $T_j=25^\circ\text{C}$)

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Zero Gate Voltage Collector Current	I_{CES}	$V_{GE}=0V$ $V_{CE}=1200V$			1.0	mA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0V$ $V_{GE}=\pm 20V$			20	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=20V$ $I_C=10\text{mA}$	5.5		8.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15V$ $I_C=10A$			3.5	V
Input capacitance	C_{ies}	$V_{GE}=0V$		1200		pF
Output capacitance	C_{oes}	$V_{CE}=10V$		250		
Reverse Transfer capacitance	C_{res}	$f=1\text{MHz}$		80		
Switching Time	Turn-on Time	t_{ON}			1.2	μs
		t_r			0.6	
	Turn-off Time	t_{OFF}			1.5	
		t_f			0.5	
	Turn-on Time	t_{ON}		0.16		μs
		t_r		0.11		
	Turn-off Time	t_{OFF}		0.30		
		t_f			0.5	

• Thermal Characteristics

Items	Symbols	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance	$R_{th(j-c)}$				0.92	$^\circ\text{C/W}$

